NSN 5961-01-449-8798

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-449-8798 **Inclosure Material:** Ceramic **Overall Length:** Between 0.370 inches and 0.400 inches **Overall Height:** Between 0.060 inches and 0.085 inches Overall Width: 0.745 inches **End Application:** A/f-18-dcn **Component Name And Quantity:** 8 semiconductor device diode **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor **Voltage Rating In Volts Per Characteristic:** 75.0 reverse breakdown voltage, dc all transistor **Current Rating Per Characteristic:** 500.00 milliamperes forward current, average preset all transistor **Power Rating Per Characteristic:** 500.0 milliwatts small-signal input power, common-collector preset all transistor **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius ambient air **Test Data Document:** 81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 16 printed circuit **Specification Data:** 81349-mil-prf-19500/474 government specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig:

Mil-std (military Standard): Mil-prf-19500 spec.

A110a0